

THE COPPER COMPANY

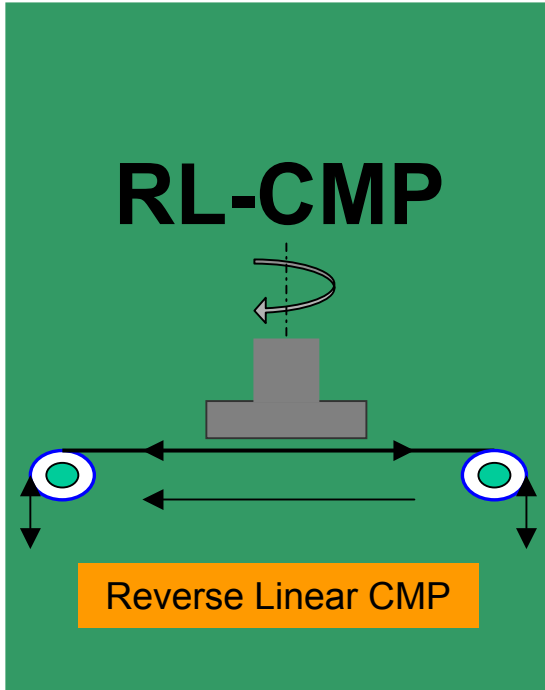


# **LuminaCu Reverse Linear CMP (RL-CMP™) Technology for < 100nm Interconnect Applications**

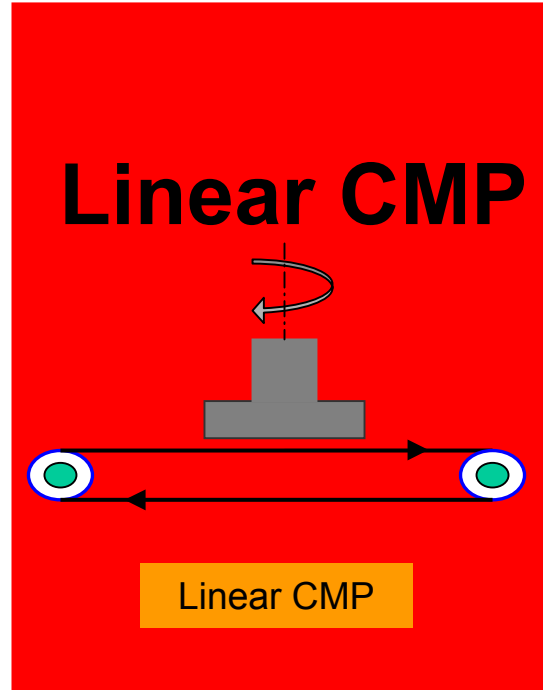
**Mukesh Desai  
Steven C. Chen  
Yuchun Wang  
Tuan Truong**

**4 September 2002  
CMPUG**

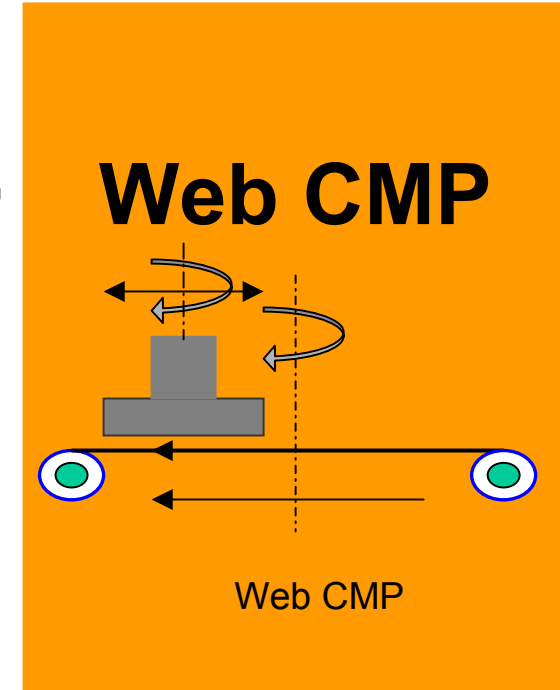
# What is RL-CMP ?



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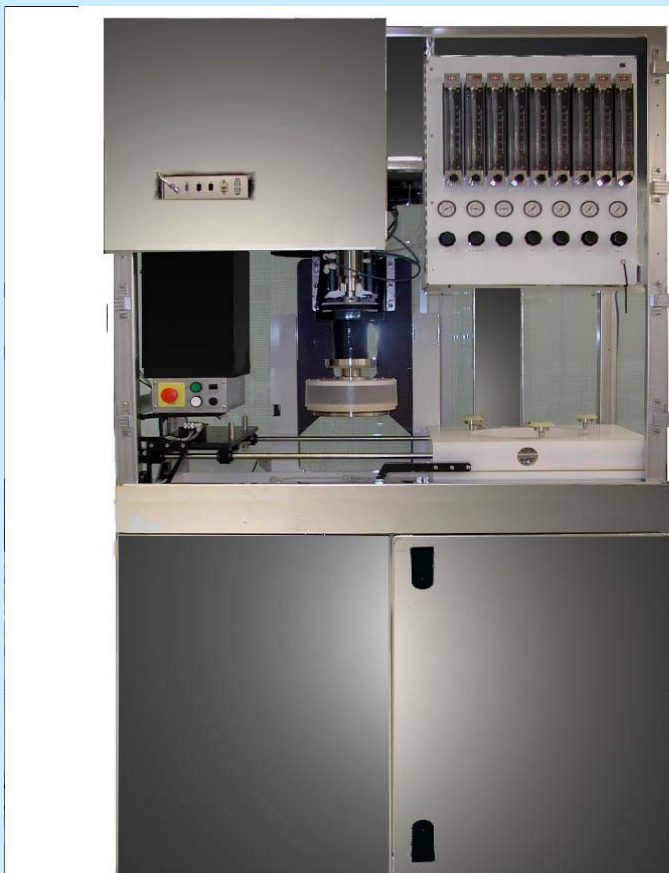


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# LuminaCu RL-CMP Module

## Key Design Features



- **Pad/Polishing Head Design**
  - Same head/pad design for Cu and STI CMP
  - No retaining ring
  - No sub-pad
  - Integrated SmartEndpoint™
- **Reverse Linear CMP Technology**
  - “Shoe Shine” belt motion
  - Belt indexing
- **Post CMP Cleaner**
  - Double sided brush clean
  - Megasonics capability

# LuminaCu RL-CMP

## Features and Benefits

### ✓ **Roll/Roll Design**

- Conventional or Fixed Abrasive Polishing Tape

### ✓ **Reverse Linear Technology**

- Up to 400ft/min
- Roll to Roll Indexing

### ✓ **Cu/Barrier Polishing Station**

- Single Wafer/Single Station
- Independent Control of Cu and Barrier Chemistries

### ✓ **Smart Endpoint**

- Multi-zone Pressure Control
- Optical Cu endpoint measurement

### ✓ **Integrated Cleaner**

- Double Brush/Megasonics
- Spin-Rinse-Dry

### ✓ **No Tape Conditioning**

- Lower Defects and Longer Tape Life

### ✓ **High Linear Velocity**

- High Polishing Rate
- Better Process Control

### ✓ **Compact Design**

- No Retaining Ring/No Hard Pad
- Small Footprint
- Lower Chemical Usage and Minimize Effluent Waste

### ✓ **Process Stability**

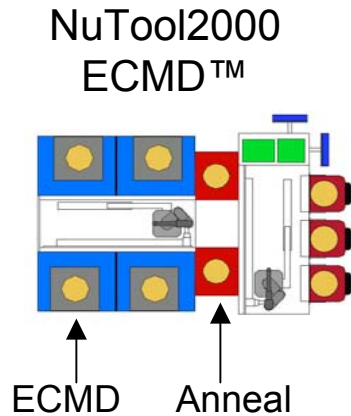
- Uniformity Control
- Dishing/Erosion Control across Wafer

### ✓ **Dry-In/Dry-Out**

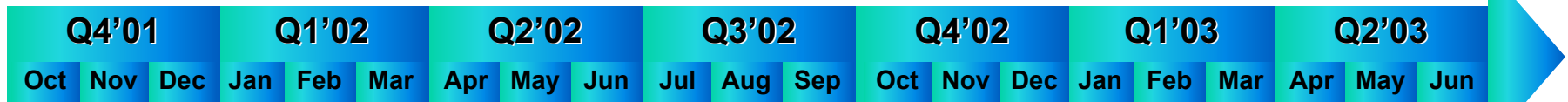
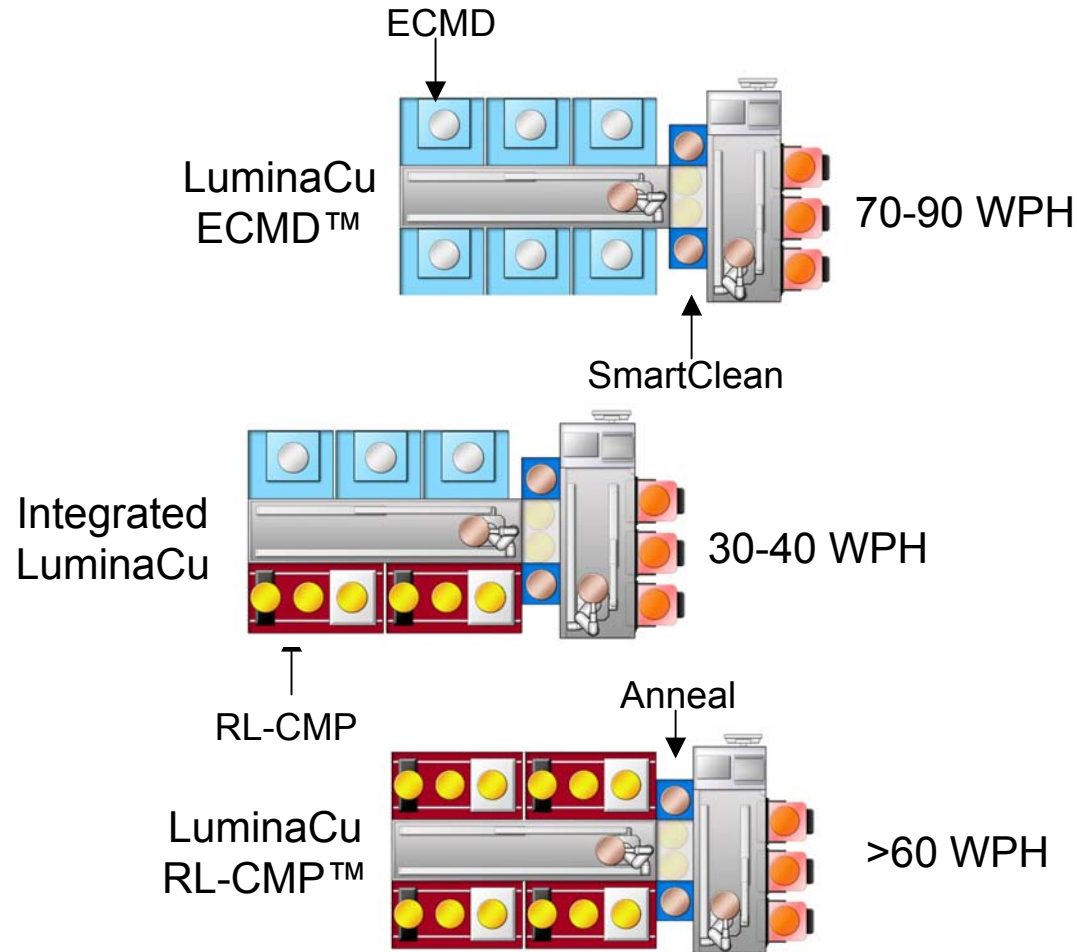
- Surface Passivation and Defect Removal

# NuTool® Product Platform Evolution

NuTool2000™ Platform

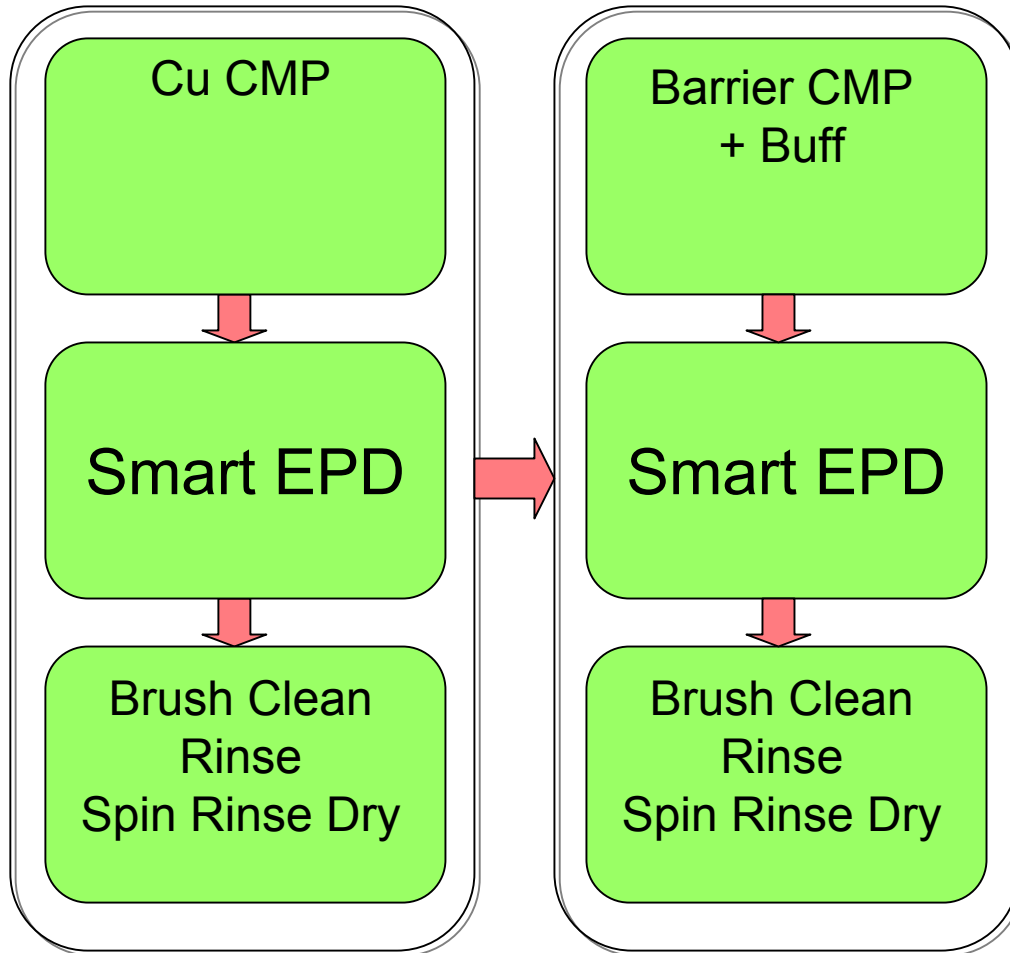


LuminaCu™ Platform



# LuminaCu RL-CMP

## Typical Process Flow



**Cu CMP Module**

**Barrier/Buffer  
CMP Module**

### Typical Results

- Cu Chemistry
  - Removal Rate (Å/min)

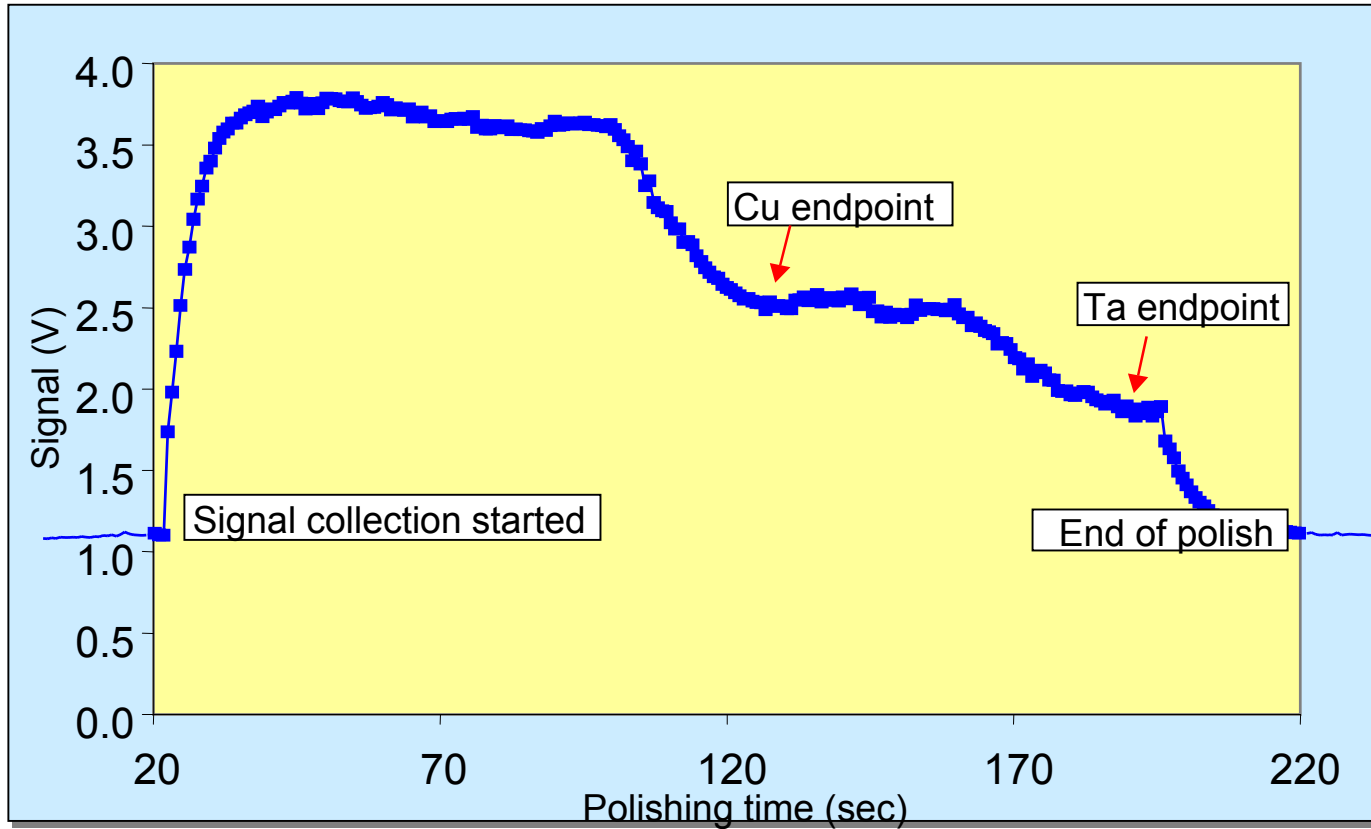
Cu	4000-6000
Ta/TaN	<100
Oxide	<100

- Barrier Chemistry
  - Removal Rate (Å/min)

Cu	<100
Ta/TaN	400-1200
Oxide	<100

# LuminaCu RL-CMP

## Endpoint Control

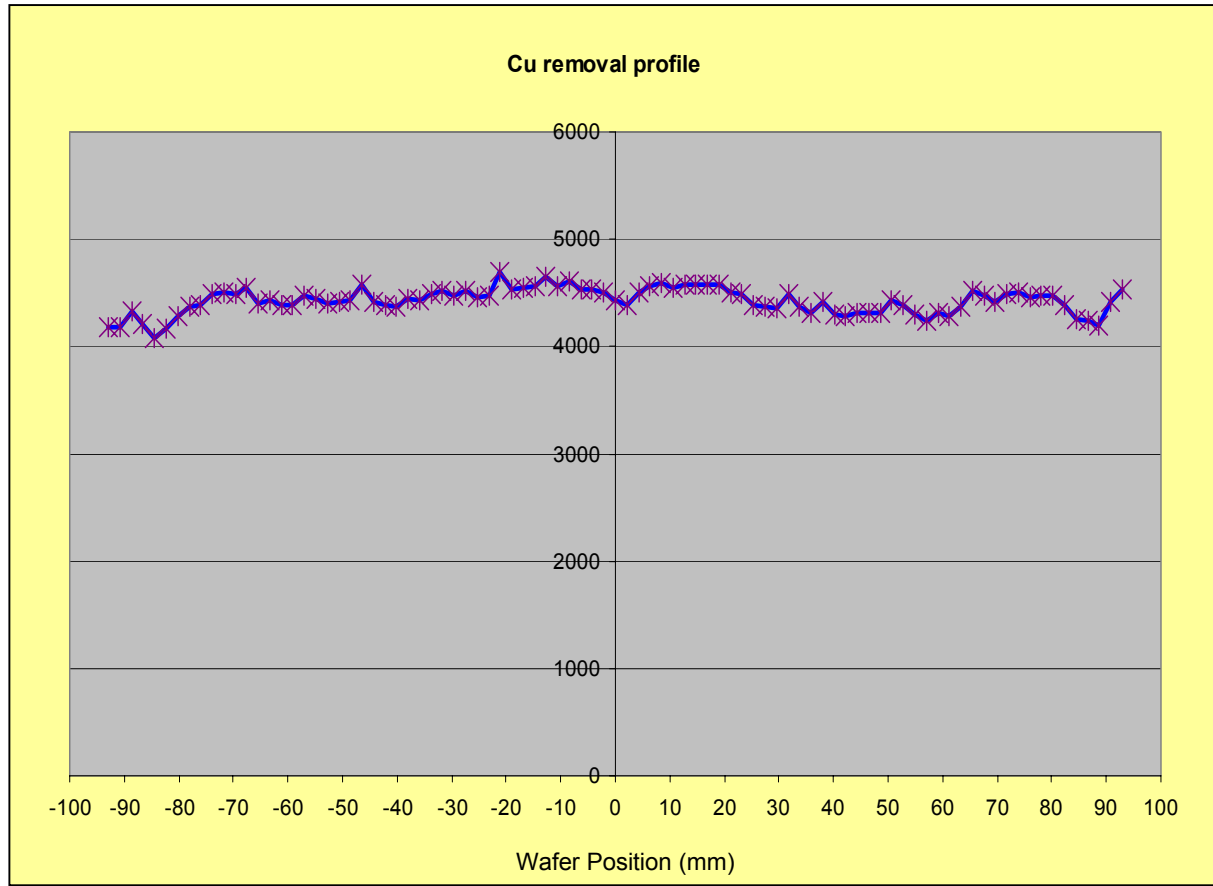


**Excellent Process Control with Easy to Use Endpoint**



# LuminaCu RL-CMP

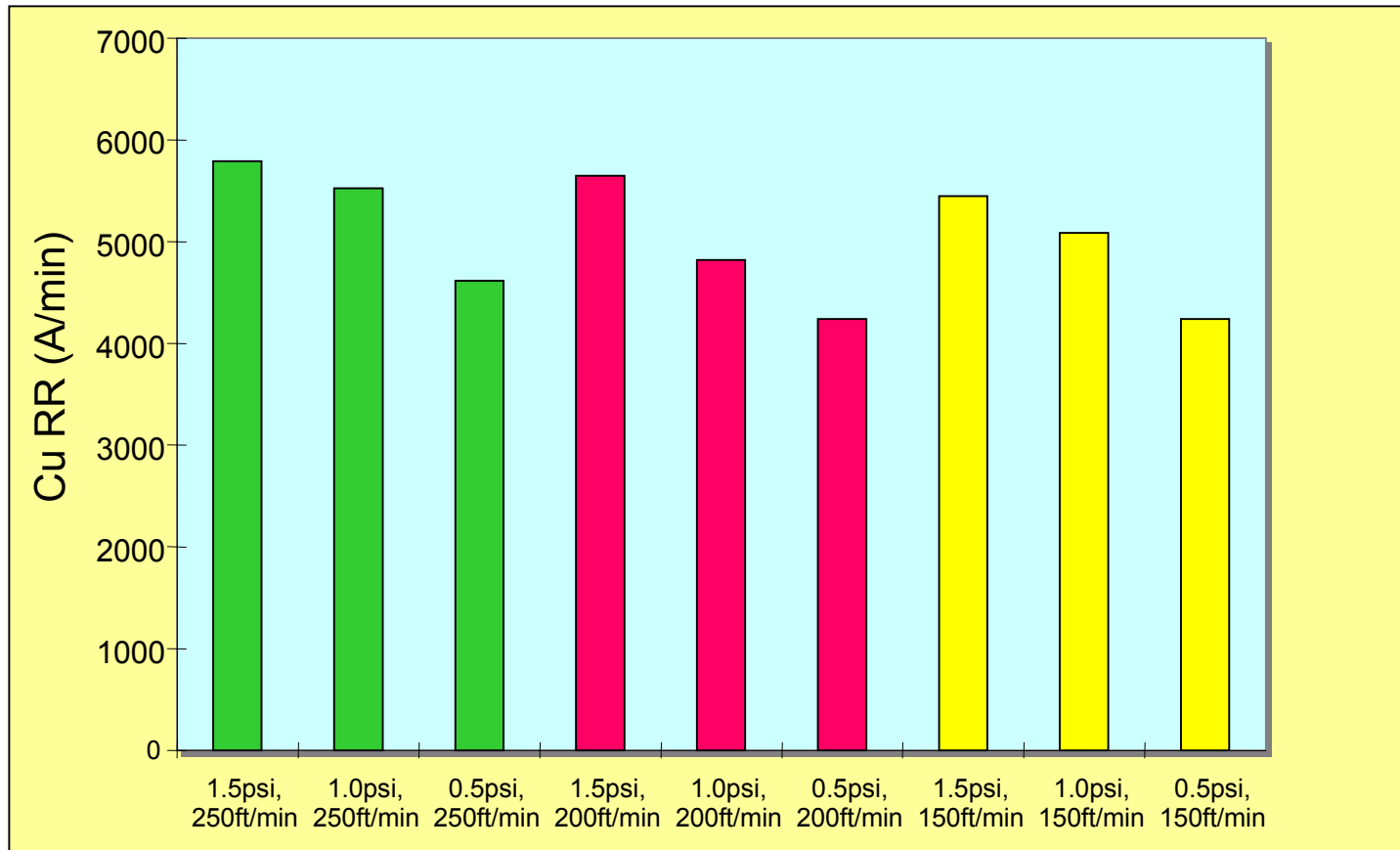
## Profile Control – Within Wafer Uniformity



**Excellent Polish Profile Control**

# LuminaCu RL-CMP

## Down Force and Belt Speed

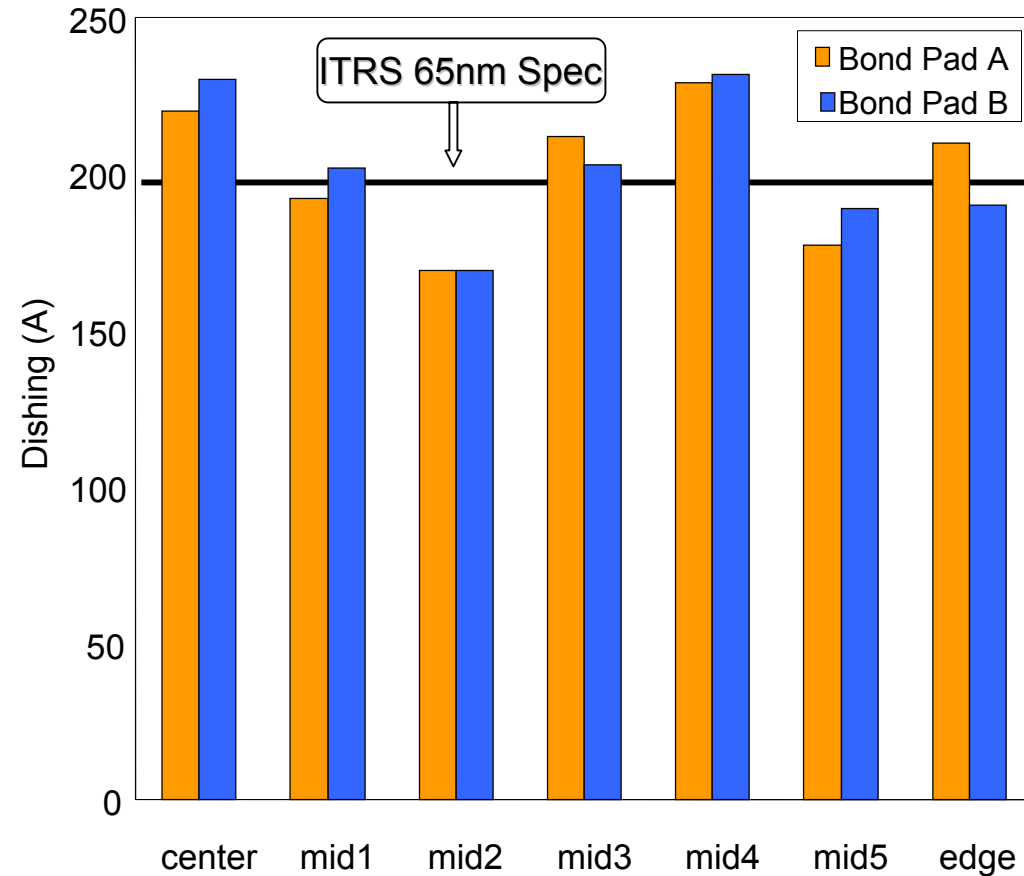


**Wider Process Window**  
**Ultra Low Polish Pressure and High Belt Speed**

# LuminaCu RL-CMP

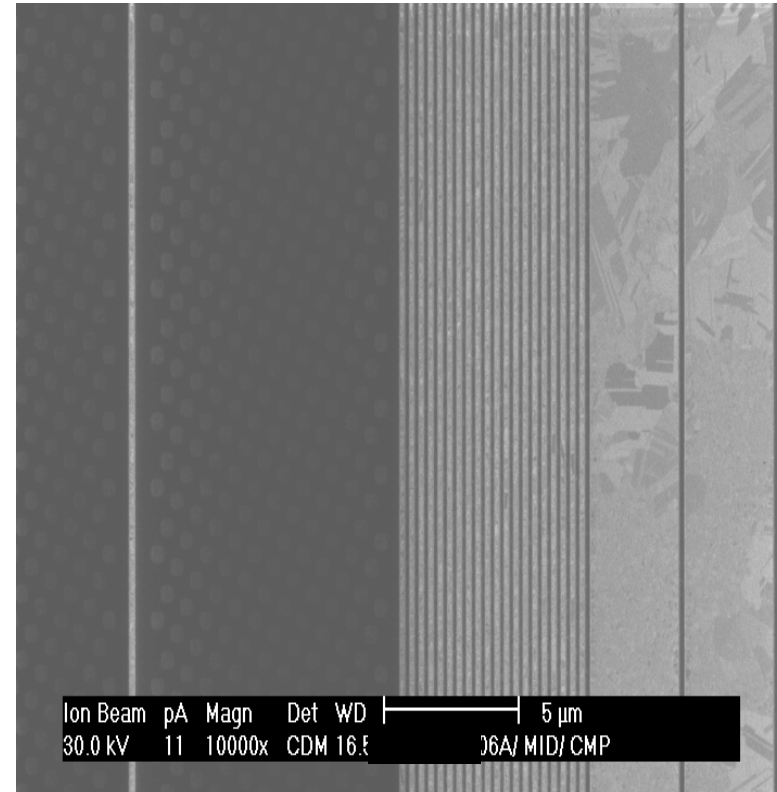
## ■ 300mm Dishing (150 $\mu$ m x 50 $\mu$ m Bond Pad)

■ Low Oxide Loss



## ■ SOD Low- $\kappa$ Integration (with ECMD)

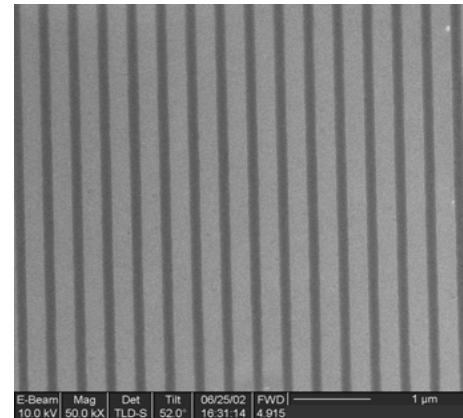
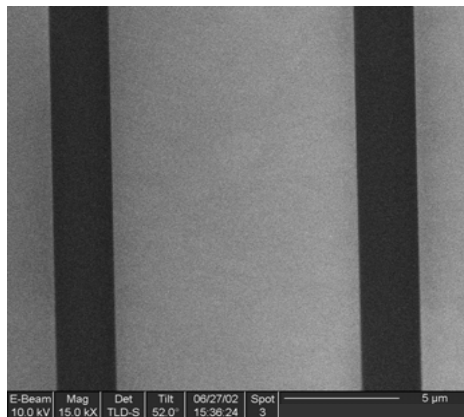
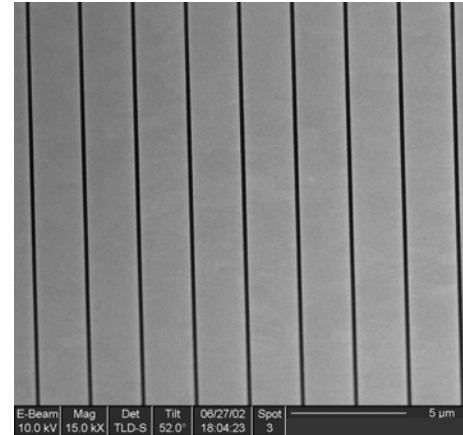
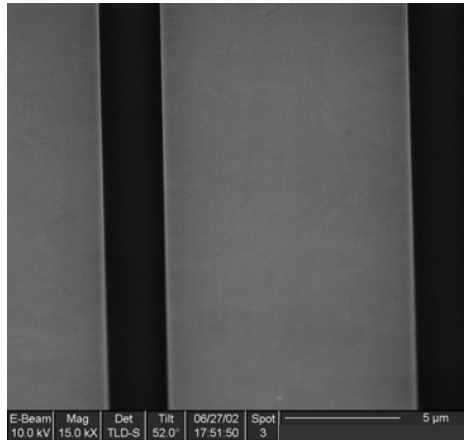
■ No Delamination



# LuminaCu RL-CMP

## Post CMP Surface Finish

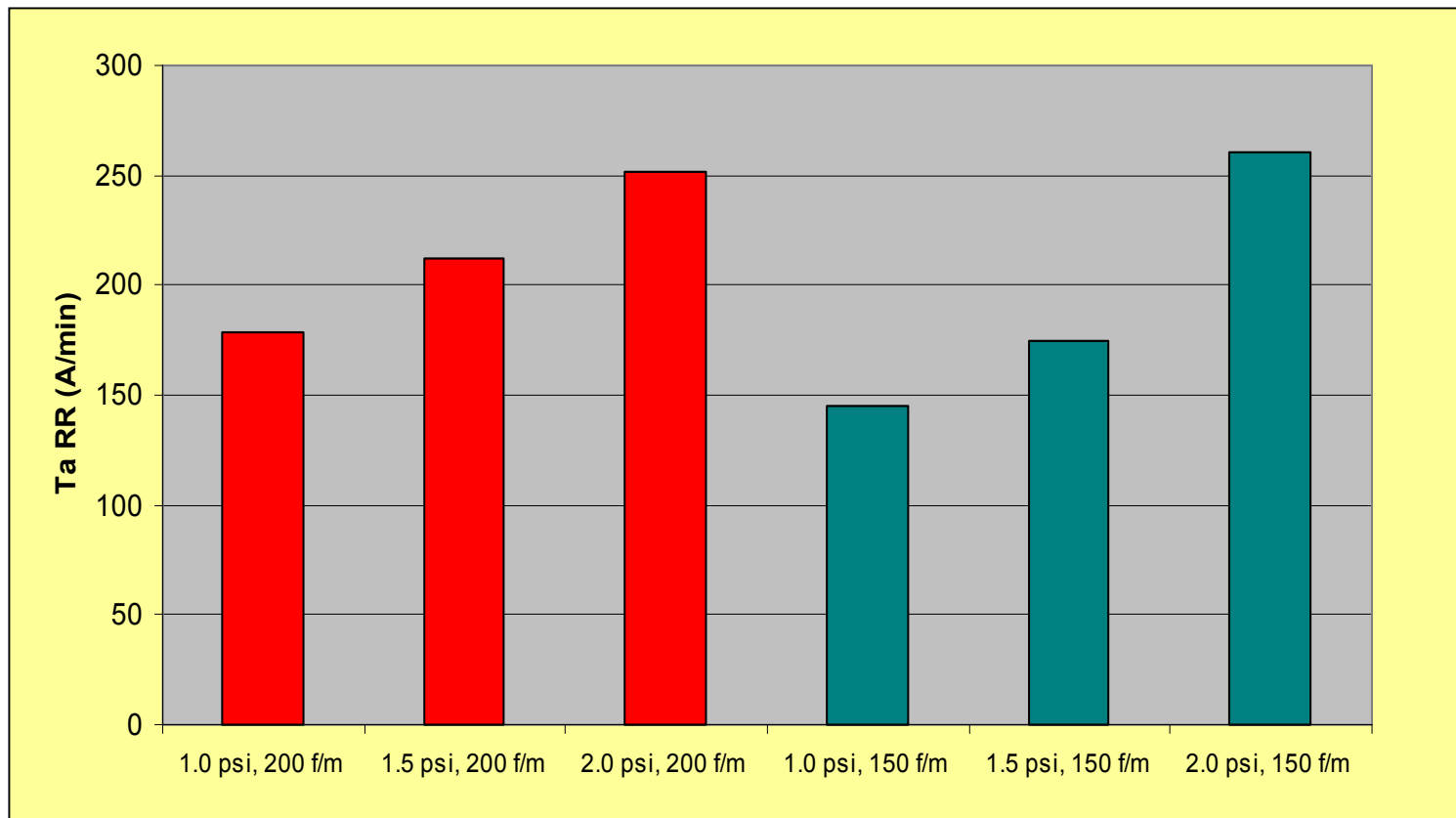
Ta removal/buffing with Politex embossed pad



**Damage Free Post CMP Surface Results**

# LuminaTa RL-CMP

## Down Force and Belt Speed



**Wider Process Window**  
**Ultra Low Polish Pressure and High Belt Speed**

# **LuminaCu RL-CMP**

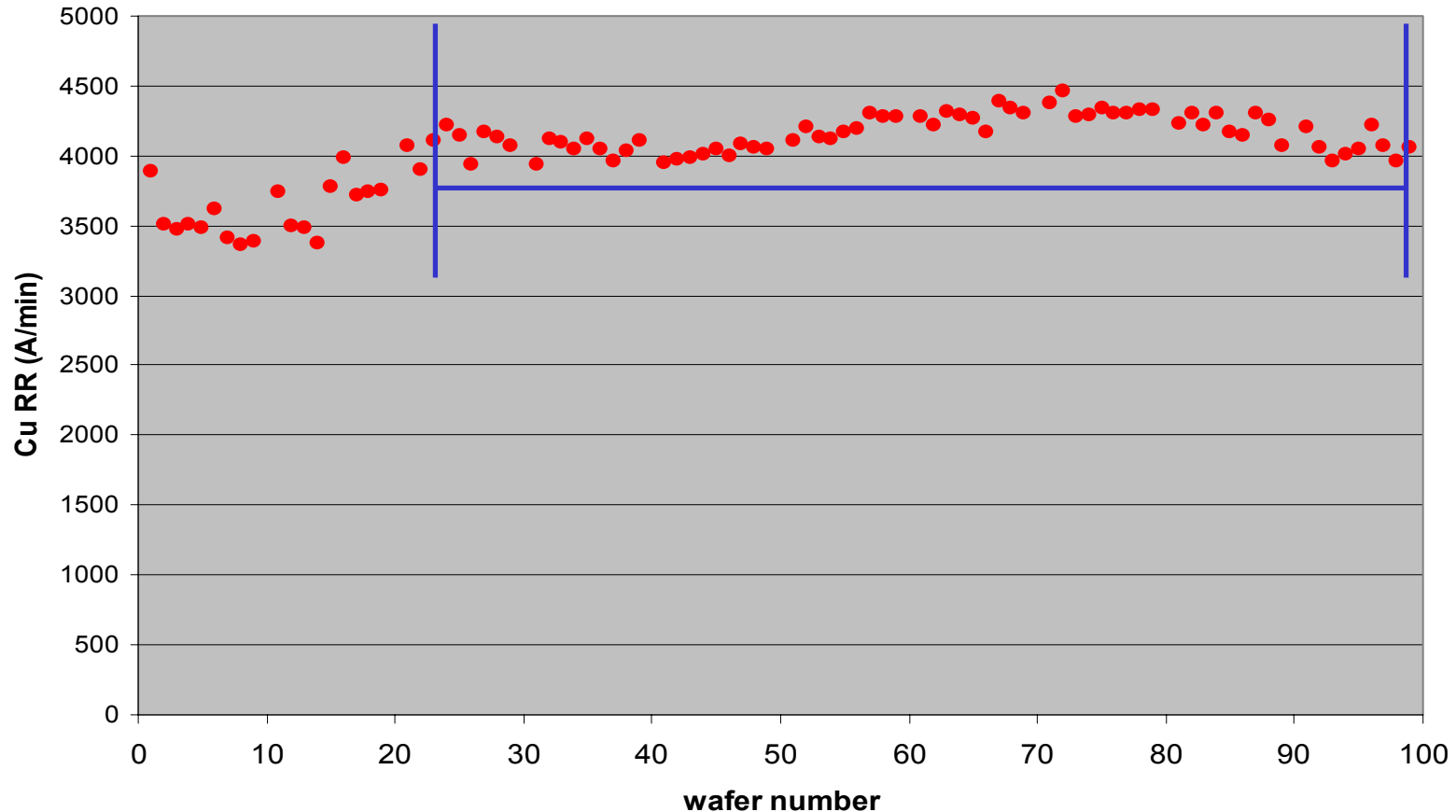
## **100 wafers Extended Run**

### **1<sup>st</sup> Observation**

# Extended Run Cu Polish

## Removal Rate Efficiency

100 wafers stability run on MWR66  
1.5 min @1.5 psi/250 f/m and 60 rpm pad with index 5 mm per wafer

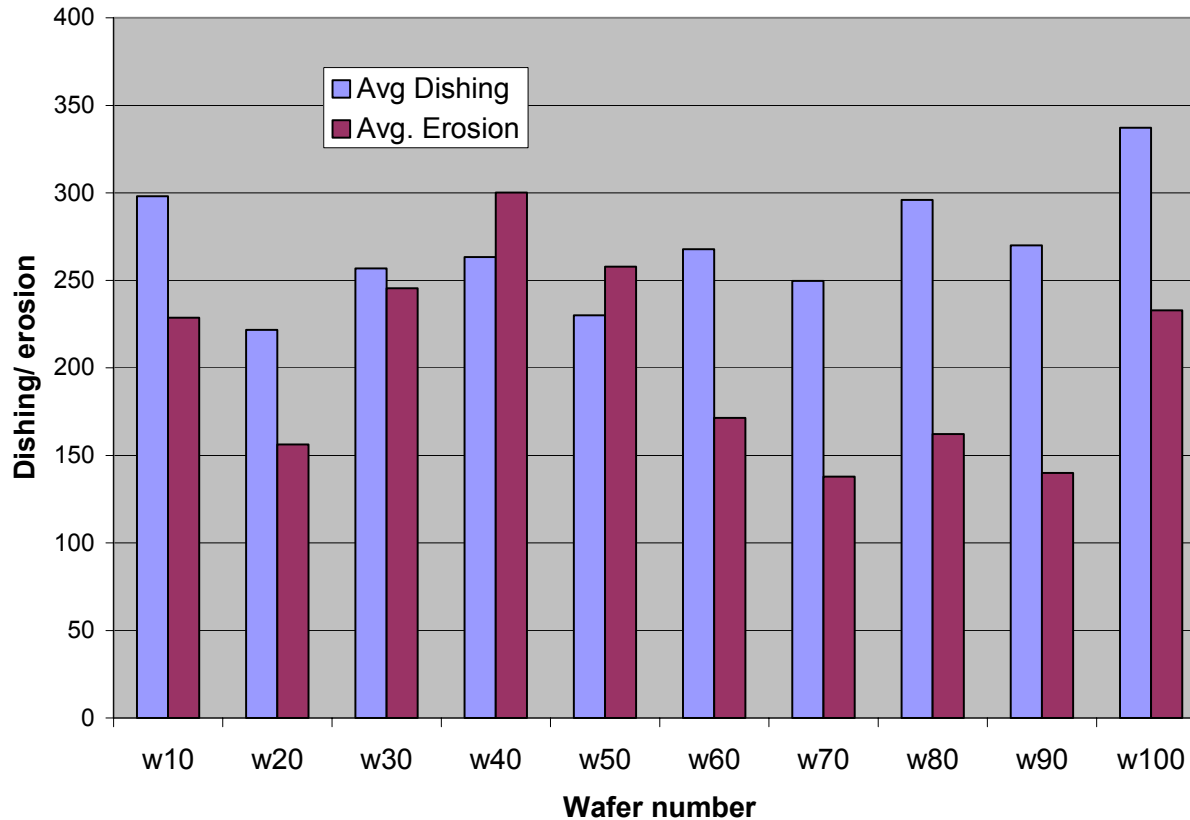


**Stable Removal Rate Performance**

# Extended Run Cu Polish

## Dishing and Erosion on Pattern Wafers

wafer dishing and erosion in 100 wafers marathon

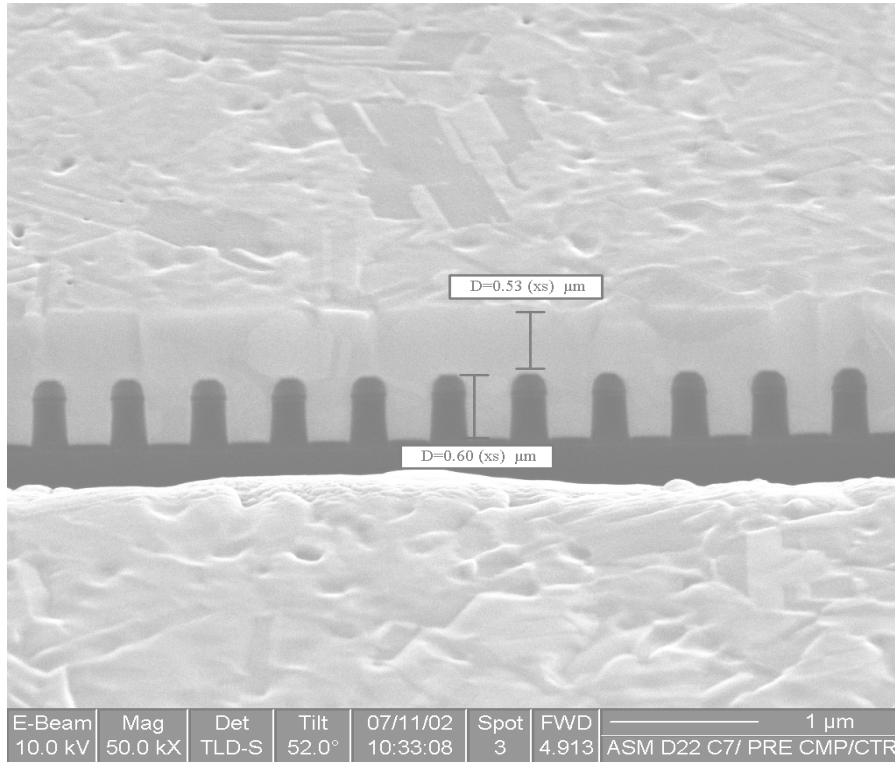


**Stable Low Dishing and Erosion Performance**

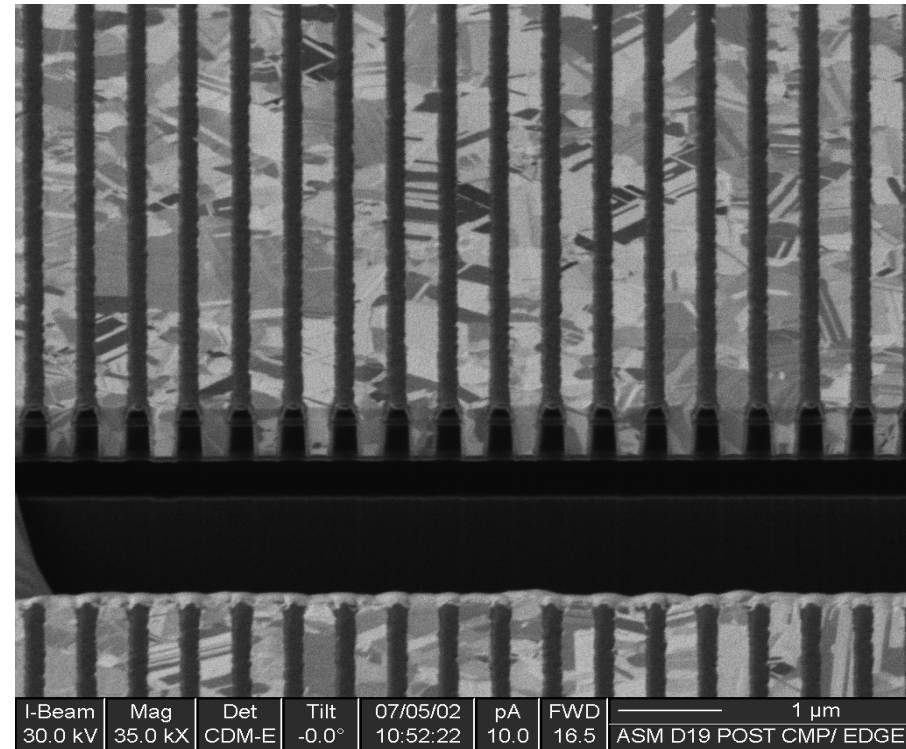


# Global Technology Alliances

NuTool Cu ECMD + ASMI Aurora™ Low-k Dielectric + NuTool Cu RL-CMP



Pre RL-CMP

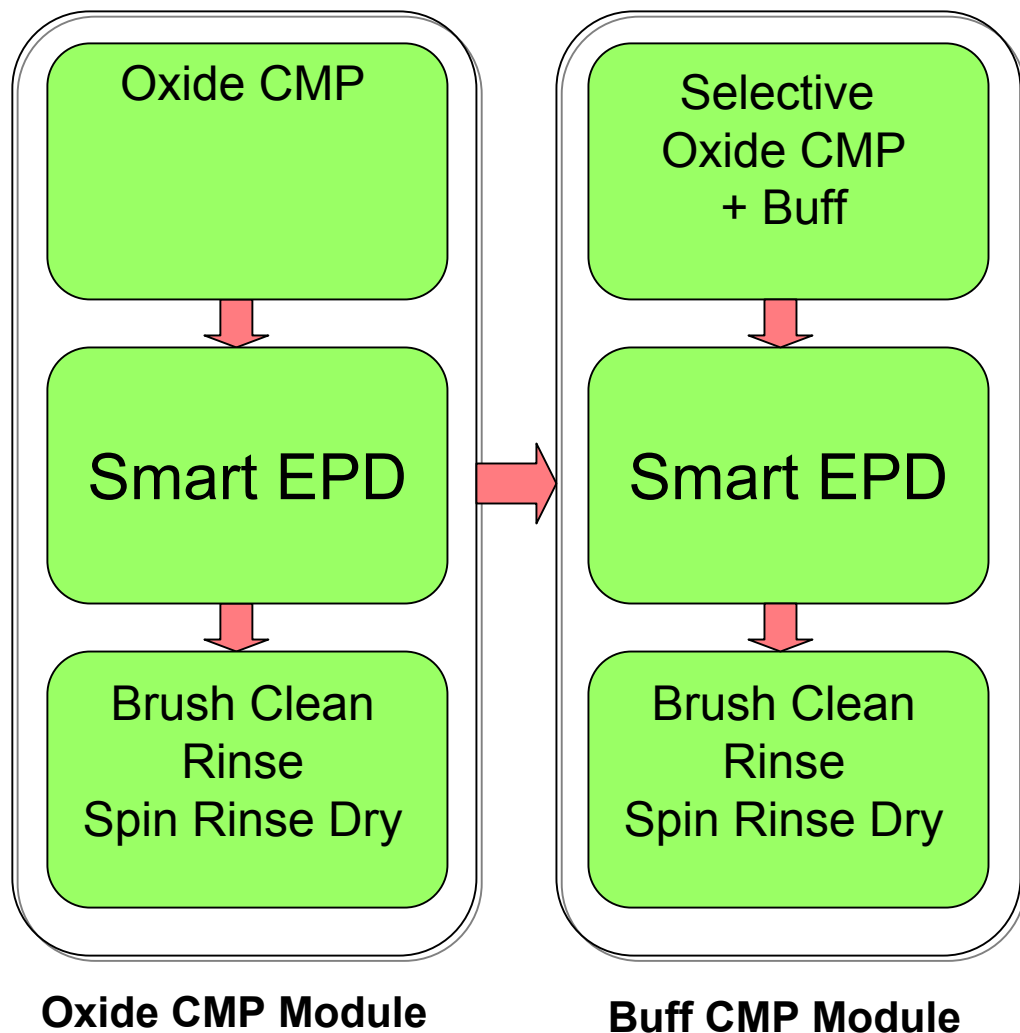


Post RL-CMP

# LuminaSTI RL-CMP

# LuminaSTI RL-CMP

## Typical Process Flow

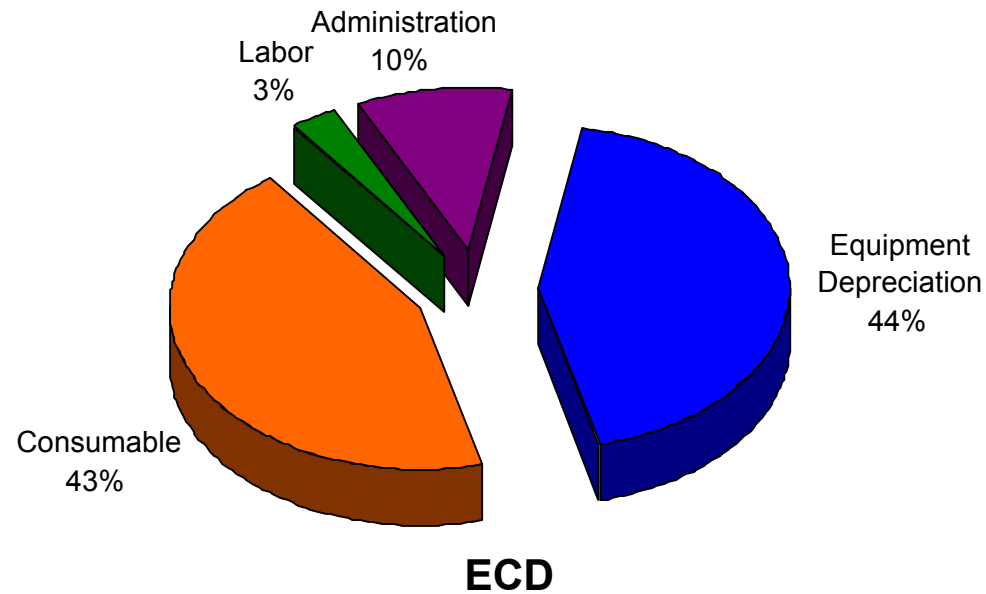
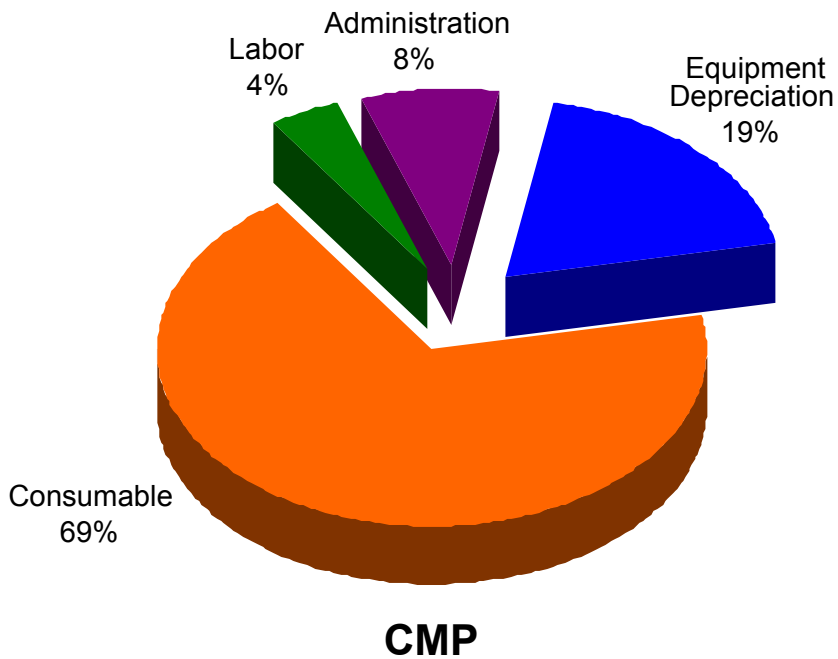
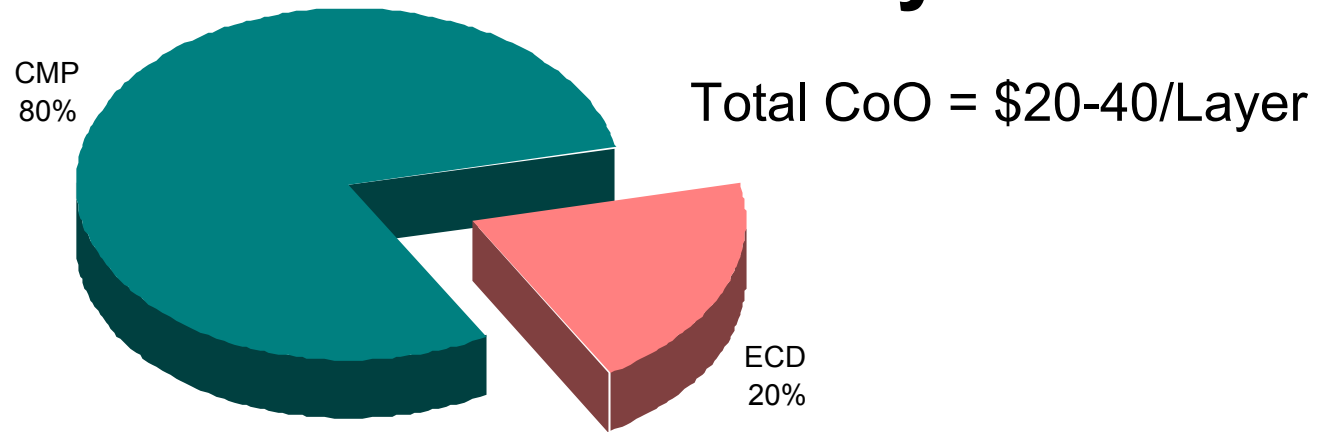


### Typical Results

- Oxide Chemistry
  - Removal Rate (Å/min)
  - Oxide 2000-3000
- Selective Chemistry
  - Removal Rate (Å/min)
  - Oxide 1000-2000
  - Nitride 50-100

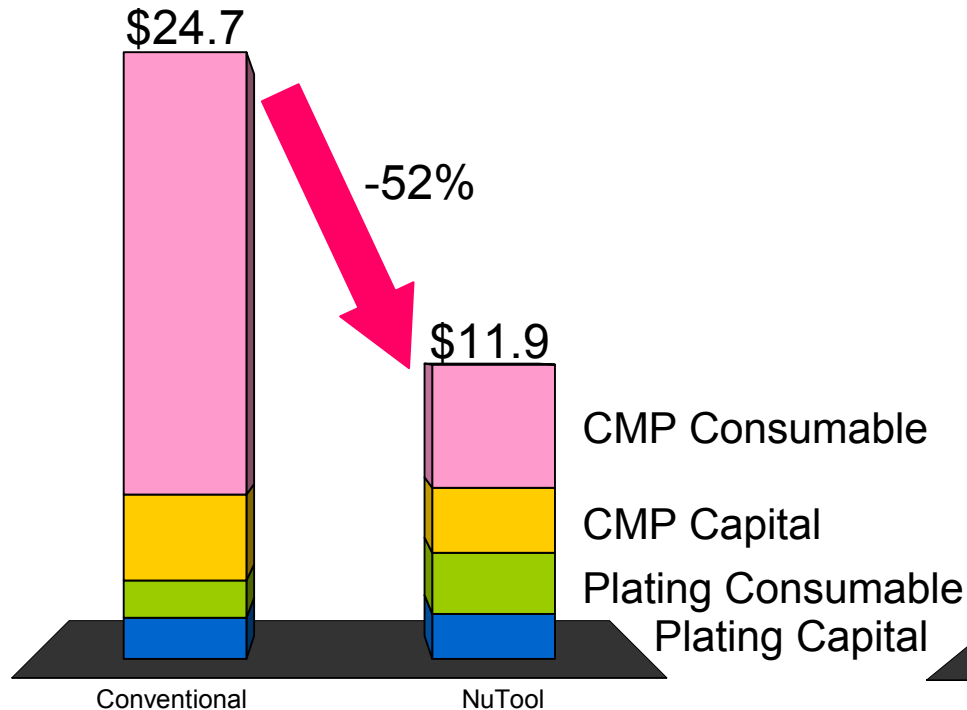
# **LuminaCu RL-CMP CoO Advantages**

# Cu ECD and CMP CoO Analysis



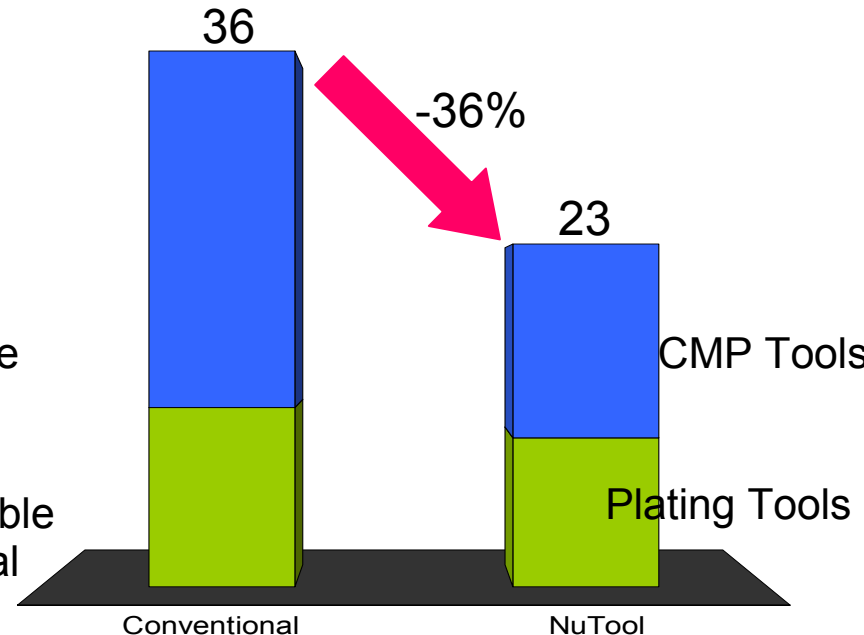
# Advantages of LuminaCu ECMD and LuminaCu RL-CMP Technologies

CoO/wafer



**Lower Cost**

Number of Tools



**Higher Productivity**

# LuminaCu Summary

## ■ Lower CoC

- Lower Cost
- Reduce Scrap
- Higher Productivity

## ■ Global Alliances and Partnerships

- Customer Support and Services
- Technology Integration

## ■ Breakthrough Cu Technologies

- Integration of Web and Linear CMP technology

**LuminaCu RL-CMP is designed  
to meet sub-micron Cu/low-k integration needs**

THE COPPER COMPANY

